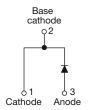
HALOGEN FREE



Vishay Semiconductors

Hyperfast Rectifier, 8 A FRED Pt®





PRIMARY CHARACTERISTICS									
I _{F(AV)}	8 A								
V_{R}	600 V								
V _F at I _F	1.4 V								
t _{rr} (typ.)	15 ns								
T _J max.	175 °C								
Package	2L TO-220AC								
Circuit configuration	Single								

FEATURES

- Hyperfast recovery time
- Benchmark ultra low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current



 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recover time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Repetitive peak reverse voltage	V_{RRM}		600	V					
Average rectified forward current	I _{F(AV)}	T _C = 143 °C	8						
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	110	Α					
Repetitive peak forward current	I _{FM}		18						
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	.,				
Forward voltage	V _F	I _F = 8 A	-	2.3	3.0	V				
		I _F = 8 A, T _J = 150 °C	-	1.4	1.7					
Develope legicome eviment	I _R	$V_R = V_R$ rated	-	0.3	50					
Reverse leakage current		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	35	500	0 μA				
Junction capacitance	C _T	V _R = 600 V	-	17	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	=.	nΗ				



DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 A, dI_F/dt = 100$	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		15	19			
Reverse recovery time		$I_F = 8 A, dI_F/dt = 100$	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		16	24			
heverse recovery time	t _{rr}	T _J = 25 °C		-	17	-	ns		
		T _J = 125 °C		-	40	-			
Peak recovery current	I _{RRM}	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs	-	2.3	-	A nC		
reak recovery current		T _J = 125 °C	$V_{\rm R} = 390 \text{ V}$	-	4.5	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C	VH = 000 V	-	20	-			
neverse recovery charge		T _J = 125 °C		-	100	-			
Reverse recovery time	t _{rr}		I _F = 8 A	-	31	-	ns		
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 600 A/\mu s$	-	12	-	Α		
Reverse recovery charge	Q _{rr}		V _R = 390 V	=	195	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance, junction-to-case	R _{thJC}		ı	1.4	2	°C/W			
Thermal resistance, junction-to-ambient per leg	R _{thJA}	Typical socket mount	-	-	70				
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-				
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device Case style 2L TO-220AC 8ETX06									

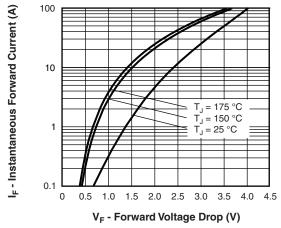


Fig. 1 - Typical Forward Voltage Drop Characteristics

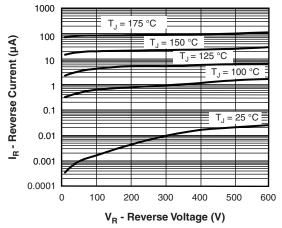


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

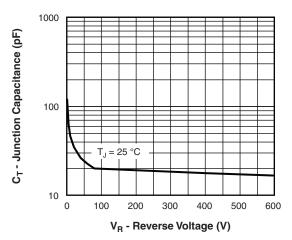


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

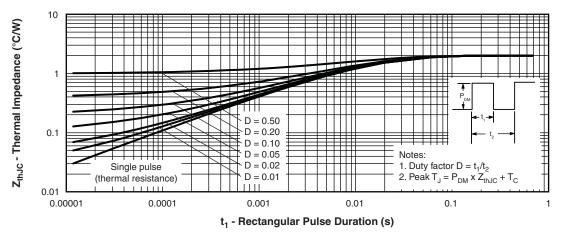


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

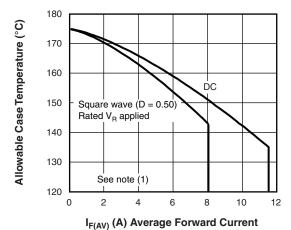


Fig. 5 - Maximum Allowable Case Temperature vs.

Average Forward Current

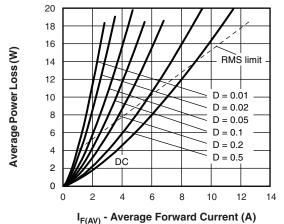


Fig. 6 - Forward Power Loss Characteristics

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_{\text{C}} = T_{\text{J}} - (\text{Pd} + \text{Pd}_{\text{REV}}) \times R_{\text{thJC}}; \\ \text{Pd} = \text{forward power loss} = I_{\text{F(AV)}} \times V_{\text{FM}} \text{ at } (I_{\text{F(AV)}}/D) \text{ (see fig. 5)}; \\ \text{Pd}_{\text{REV}} = \text{inverse power loss} = V_{\text{R1}} \times I_{\text{R}} \text{ (1 - D)}; I_{\text{R}} \text{ at } V_{\text{R1}} = \text{rated } V_{\text{R}} \\ \end{array}$

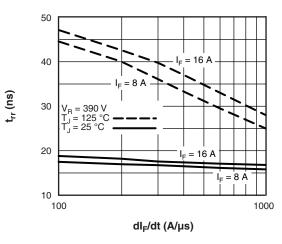


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

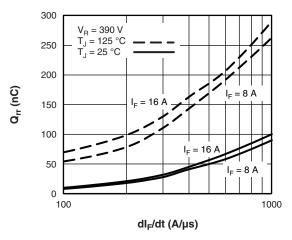
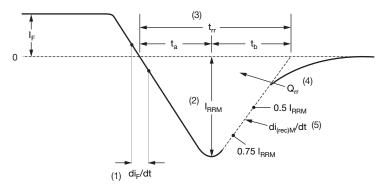


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

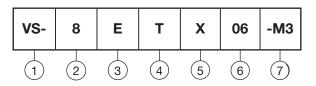
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

3 - E = single

- T = TO-220, D²PAK (TO-263AB)

5 - X = hyperfast rectifier

6 - Voltage rating (06 = 600 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

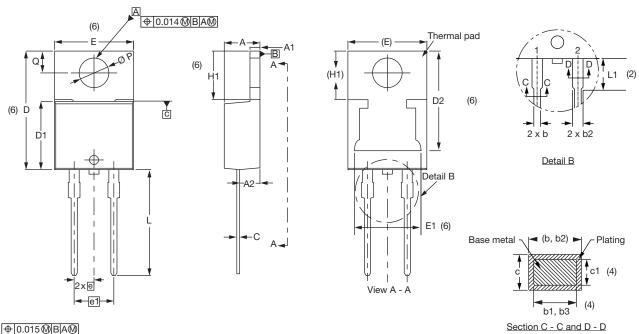
ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-8ETX06-M3	50	1000	Antistatic plastic tube						

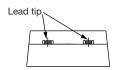
LINKS TO RELATED DOCUMENTS								
Dimensions <u>www.vishay.com/doc?96156</u>								
Part marking information	www.vishay.com/doc?95391							



2L TO-220AC

DIMENSIONS in millimeters and inches





Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355				•	•			

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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Vishay

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